

FEATURES

- * 0.27 INCH (7.0 mm) DIGIT HEIGHT.
- * CONTINUOUS UNIFORM SEGMENTS.
- * LOW POWER REQUIREMENT.
- * EXCELLENT CHARACTERS APPEARANCE.
- * HIGH BRIGHTNESS & HIGH CONTRAST.
- * WIDE VIEWING ANGLE.
- * SOLID STATE RELIABILITY.

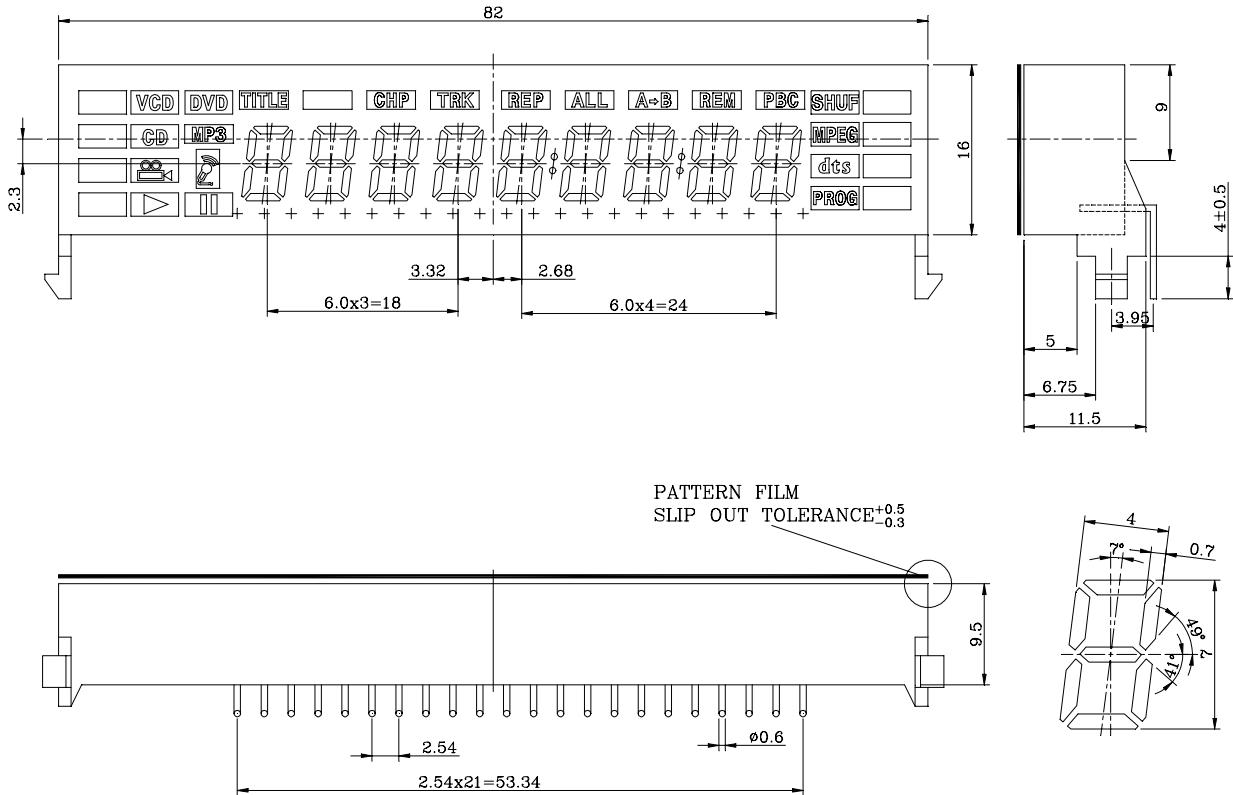
DESCRIPTION

The LTG-Y2K31M is a 0.27 inch (7.0 mm) digit height seven-segment display. The device is multi-color applicable display. The green LED chips, which are made from GaP on a transparent GaP substrate. The red orange & amber LED chips, which are made from GaAsP on a transparent GaP.

DEVICE

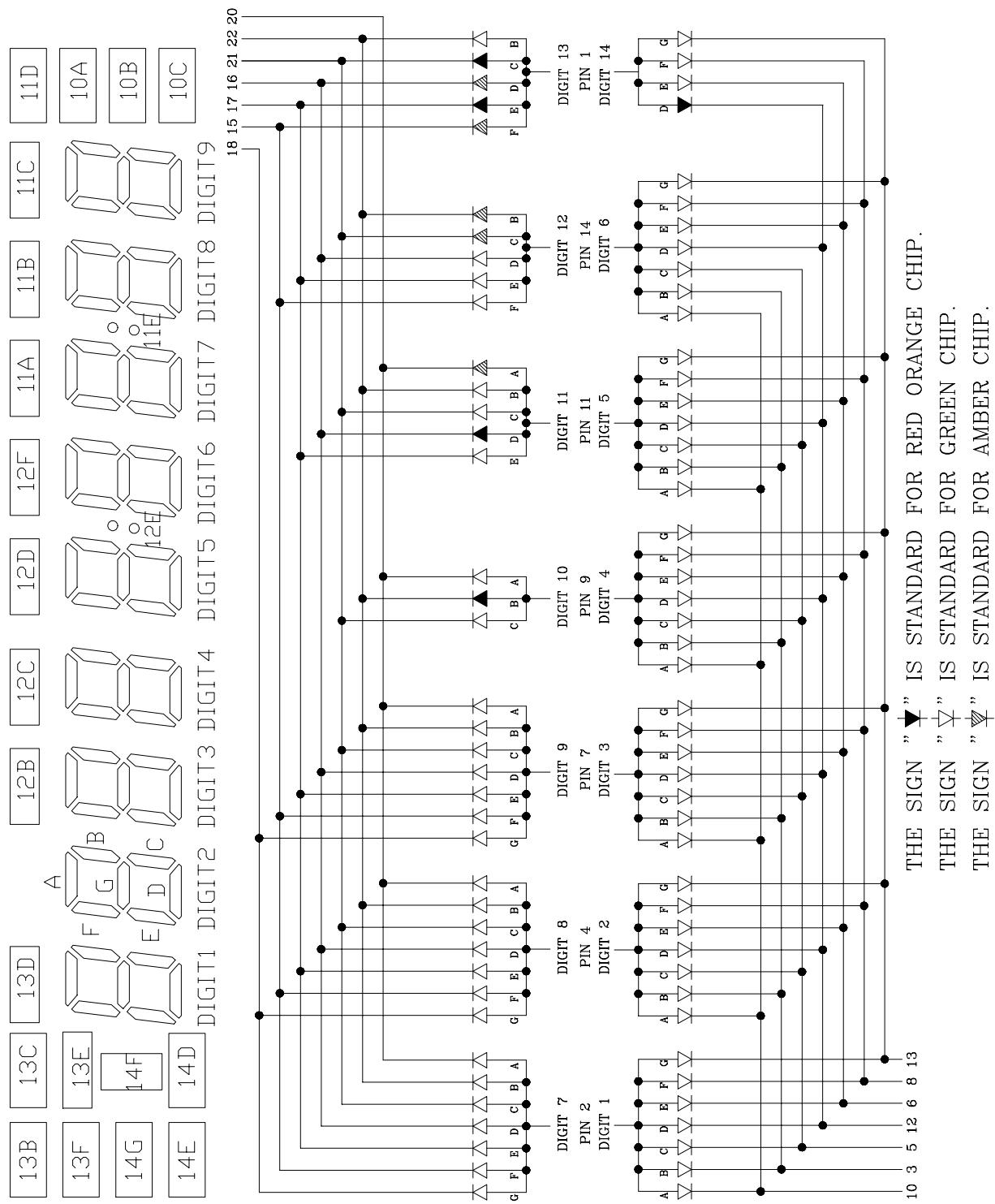
| PART NO. | DESCRIPTION |
|-------------|------------------------|
| MULTI-COLOR | |
| LTG-Y2K31M | Multiplex Common Anode |

PACKAGE DIMENSIONS



NOTES: All dimensions are in millimeters. Tolerances are ± 0.25 mm unless otherwise noted.

INTERNAL CIRCUIT DIAGRAM



THE SIGN "▼" IS STANDARD FOR RED ORANGE CHIP.
THE SIGN "▽" IS STANDARD FOR GREEN CHIP.
THE SIGN "▽▽" IS STANDARD FOR AMBER CHIP.

PIN CONNECTION

| No. | CONNECTION |
|-----|----------------------------|
| 1 | COMMON ANODE (DIGIT 13,14) |
| 2 | COMMON ANODE (DIGIT 1,7) |
| 3 | CATHODE B |
| 4 | COMMON ANODE (DIGIT 2,8) |
| 5 | CATHODE C |
| 6 | CATHODE E |
| 7 | COMMON ANODE (DIGIT 3,9) |
| 8 | CATHODE F |
| 9 | COMMON ANODE (DIGIT 4,10) |
| 10 | CATHODE A |
| 11 | COMMON ANODE (DIGIT 5,11) |
| 12 | CATHODE D |
| 13 | CATHODE G |
| 14 | COMMON ANODE (DIGIT 6,12) |
| 15 | CATHODE F |
| 16 | CATHODE D |
| 17 | CATHODE E |
| 18 | CATHODE G |
| 19 | NO CONNECTION |
| 20 | CATHODE A |
| 21 | CATHODE C |
| 22 | CATHODE B |

ABSOLUTE MAXIMUM RATING AT T_a=25°C

| PARAMETER | GREEN | RED ORANGE | AMBER | UNIT |
|---|-------|-----------------|-------|-------|
| Power Dissipation Per Chip | 75 | 75 | 75 | mW |
| Peak Forward Current Per Chip (1/10 Duty Cycle, 0.1ms Pulse Width) | 100 | 100 | 100 | mA |
| Continuous Forward Current Per Chip | 25 | 25 | 25 | mA |
| Derating Linear From 25°C Per Chip | 0.28 | 0.28 | 0.28 | mA/°C |
| Reverse Voltage Per Chip | 5 | 5 | 5 | V |
| Operating Temperature Range | | -35°C to +105°C | | |
| Storage Temperature Range | | -35°C to +105°C | | |
| Solder Temperature: max 260°C for max 3sec at 1.6mm below seating plane | | | | |

ELECTRICAL / OPTICAL CHARACTERISTICS AT T_a=25°C

DIGIT(GREEN)

| PARAMETER | SYMBOL | MIN. | TYP. | MAX. | UNIT | TEST CONDITION |
|--|------------------|------|------|------|------|----------------------|
| Average Luminous Intensity Per Segment | I _v | | 930 | | μcd | I _F =10mA |
| Peak Emission Wavelength | λ _p | | 565 | | nm | I _F =20mA |
| Spectral Line Half-Width | Δλ | | 30 | | nm | I _F =20mA |
| Dominant Wavelength | λ _d | | 569 | | nm | I _F =20mA |
| Forward Voltage Per Chip | V _F | | 2.1 | 2.6 | V | I _F =20mA |
| Reverse Current Per Chip | I _R | | | 100 | μA | V _R =5V |
| Luminous Intensity Matching Ratio | I _{v-m} | | | 2:1 | | I _F =10mA |

ICON(GREEN)

| PARAMETER | SYMBOL | MIN. | TYP. | MAX. | UNIT | TEST CONDITION |
|--|------------------|------|------|------|------|----------------------|
| Average Luminous Intensity Per Segment | I _v | | 1170 | | μcd | I _F =10mA |
| Peak Emission Wavelength | λ _p | | 565 | | nm | I _F =20mA |
| Spectral Line Half-Width | Δλ | | 30 | | nm | I _F =20mA |
| Dominant Wavelength | λ _d | | 569 | | nm | I _F =20mA |
| Forward Voltage Per Chip | V _F | | 2.1 | 2.6 | V | I _F =20mA |
| Reverse Current Per Chip | I _R | | | 100 | μA | V _R =5V |
| Luminous Intensity Matching Ratio | I _{v-m} | | | 2:1 | | I _F =10mA |

ICON(RED ORANGE)

| PARAMETER | SYMBOL | MIN. | TYP. | MAX. | UNIT | TEST CONDITION |
|--|------------------|------|------|------|------|----------------------|
| Average Luminous Intensity Per Segment | I _v | | 1060 | | μcd | I _F =10mA |
| Peak Emission Wavelength | λ _p | | 630 | | nm | I _F =20mA |
| Spectral Line Half-Width | Δλ | | 40 | | nm | I _F =20mA |
| Dominant Wavelength | λ _d | | 621 | | nm | I _F =20mA |
| Forward Voltage Per Chip | V _F | | 2.0 | 2.6 | V | I _F =20mA |
| Reverse Current Per Chip | I _R | | | 100 | μA | V _R =5V |
| Luminous Intensity Matching Ratio | I _{v-m} | | | 2:1 | | I _F =10mA |

ICON(AMBER)

| PARAMETER | SYMBOL | MIN. | TYP. | MAX. | UNIT | TEST CONDITION |
|--|------------------|------|------|------|------|----------------------|
| Average Luminous Intensity Per Segment | I _v | | 650 | | μcd | I _F =10mA |
| Peak Emission Wavelength | λ _p | | 610 | | nm | I _F =20mA |
| Spectral Line Half-Width | Δλ | | 35 | | nm | I _F =20mA |
| Dominant Wavelength | λ _d | | 602 | | nm | I _F =20mA |
| Forward Voltage Per Chip | V _F | | 2.1 | 2.6 | V | I _F =20mA |
| Reverse Current Per Chip | I _R | | | 100 | μA | V _R =5V |
| Luminous Intensity Matching Ratio | I _{v-m} | | | 2:1 | | I _F =10mA |

Note: Luminous intensity is measured with a light sensor and filter combination that approximates the CIE (Commission Internationale De L'Eclairage) eye-response curve.

TYPICAL ELECTRICAL / OPTICAL CHARACTERISTIC CURVES

(25°C Ambient Temperature Unless Otherwise Noted)

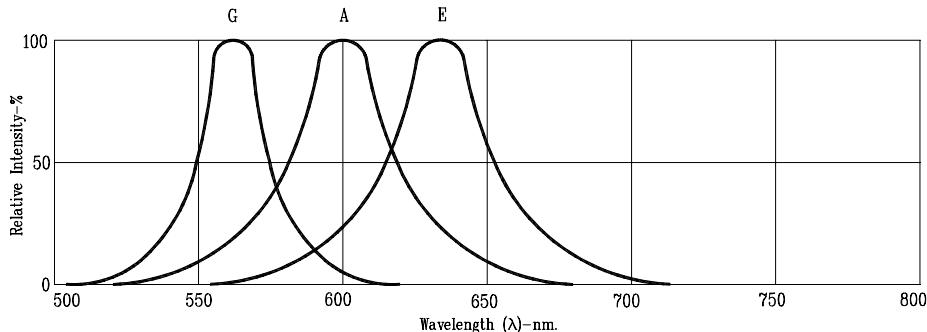
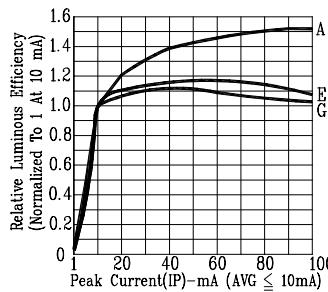
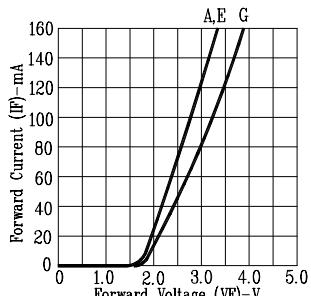
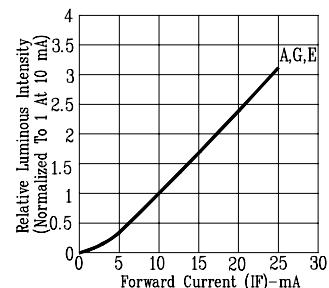
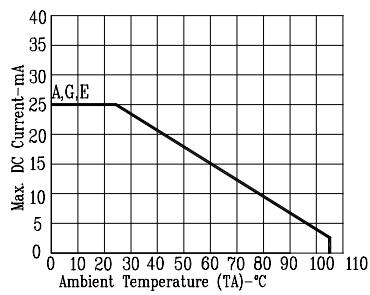
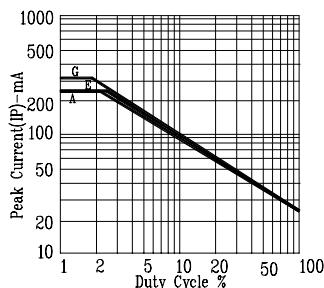


Fig1. RELATIVE INTENSITY VS. WAVELENGTH

Fig2. RELATIVE LUMINOUS EFFICIENCY
(LUMINOUS INTENSITY PER UNIT
CURRENT) VS. PEAK CURRENT
(REFRESH RATE 1KHz)Fig3. FORWARD CURRENT VS.
FORWARD VOLTAGEFig4. RELATIVE LUMINOUS INTENSITY
VS. FORWARD CURRENTFig5. MAX. ALLOWABLE DC CURRENT
VS. AMBIENT TEMPERATURE.Fig6. MAX. PEAK CURRENT VS.
DUTY CYCLE %
(REFRESH RATE 1KHz)

NOTE: A=AMBER G=GREEN E=RED ORANGE